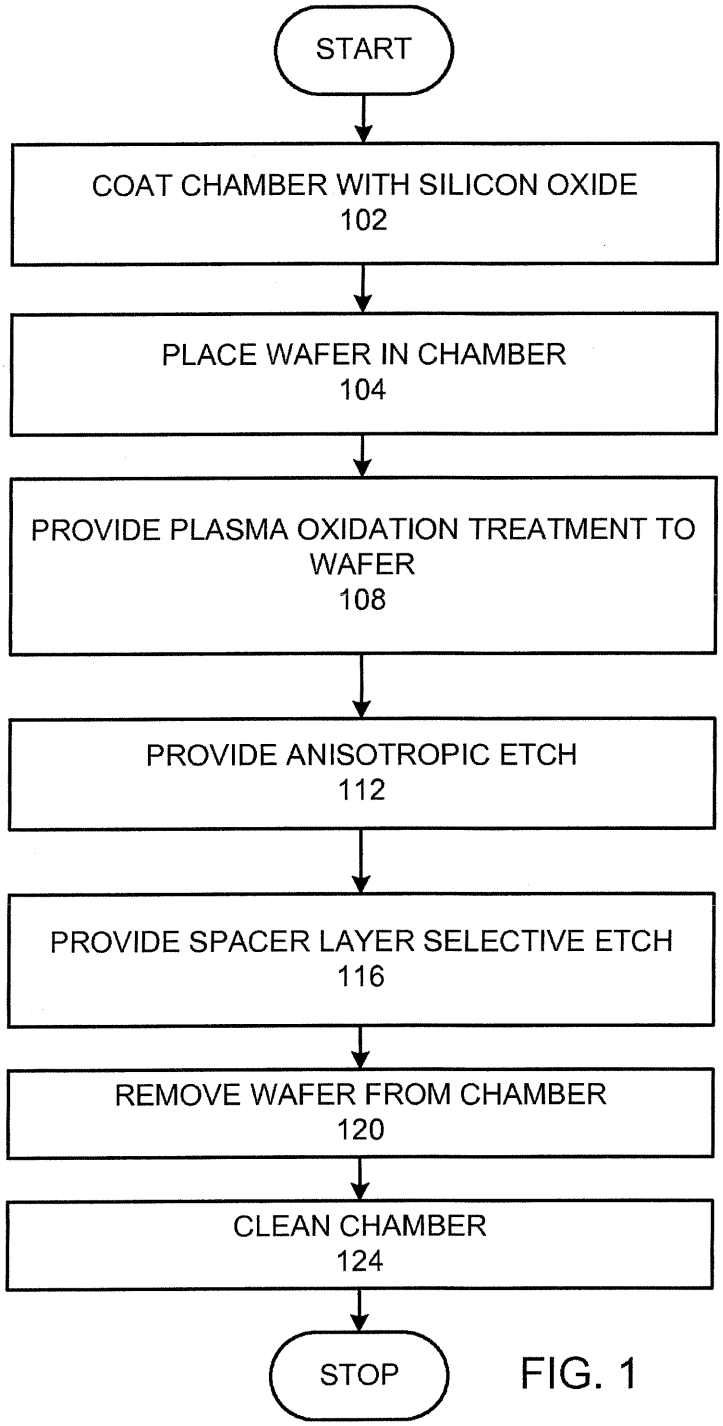

START
COAT CHAMBER WITH SILICON OXIDE
102
PLACE WAFER IN CHAMBER
104
PROVIDE PLASMA OXIDATION TREATMENT TO WAFER
108
PROVIDE ANISOTROPIC ETCH
112
PROVIDE SPACER LAYER SELECTIVE ETCH
116
REMOVE WAFER FROM CHAMBER
120
CLEAN CHAMBER
124
STOP

FIG. 1

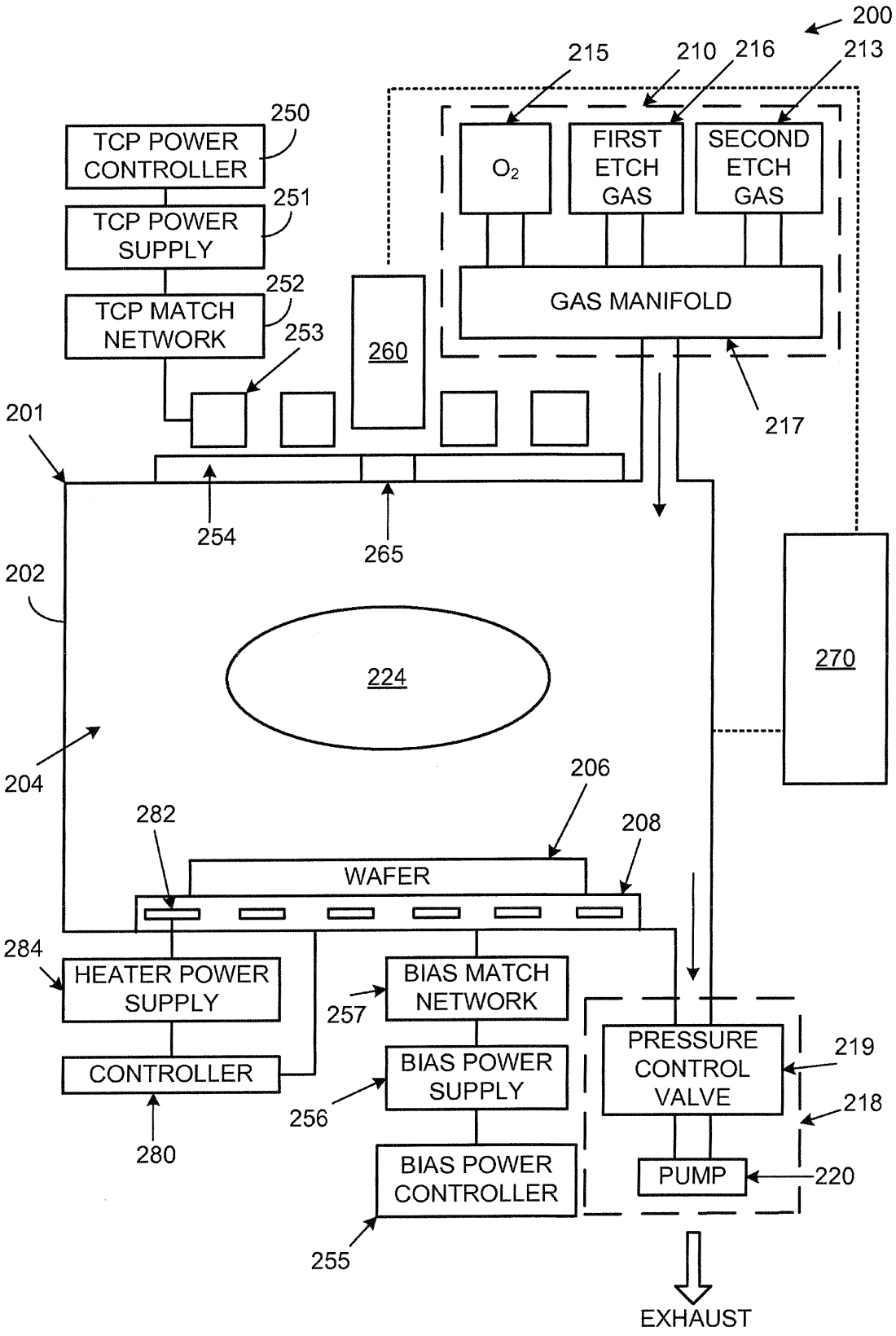

200
215
210
216
213
250
TCP POWER CONTROLLER
251
TCP POWER SUPPLY
252
TCP MATCH NETWORK
253
O_2
FIRST ETCH GAS
SECOND ETCH GAS
GAS MANIFOLD
260
217
201
254
265
202
224
270
204
206
282
208
WAFER
284
HEATER POWER SUPPLY
CONTROLLER
280
257
BIAS MATCH NETWORK
256
BIAS POWER SUPPLY
BIAS POWER CONTROLLER
255
PRESSURE CONTROL VALVE
219
218
PUMP
220
EXHAUST

FIG. 2

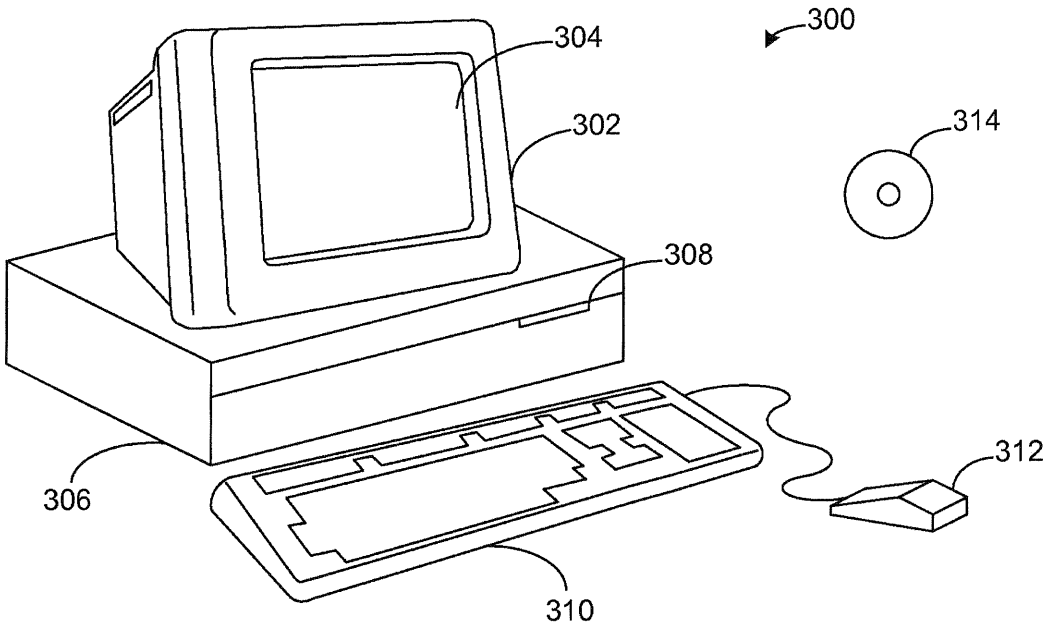

300
304
302
314
308
312
306
310

FIG. 3A

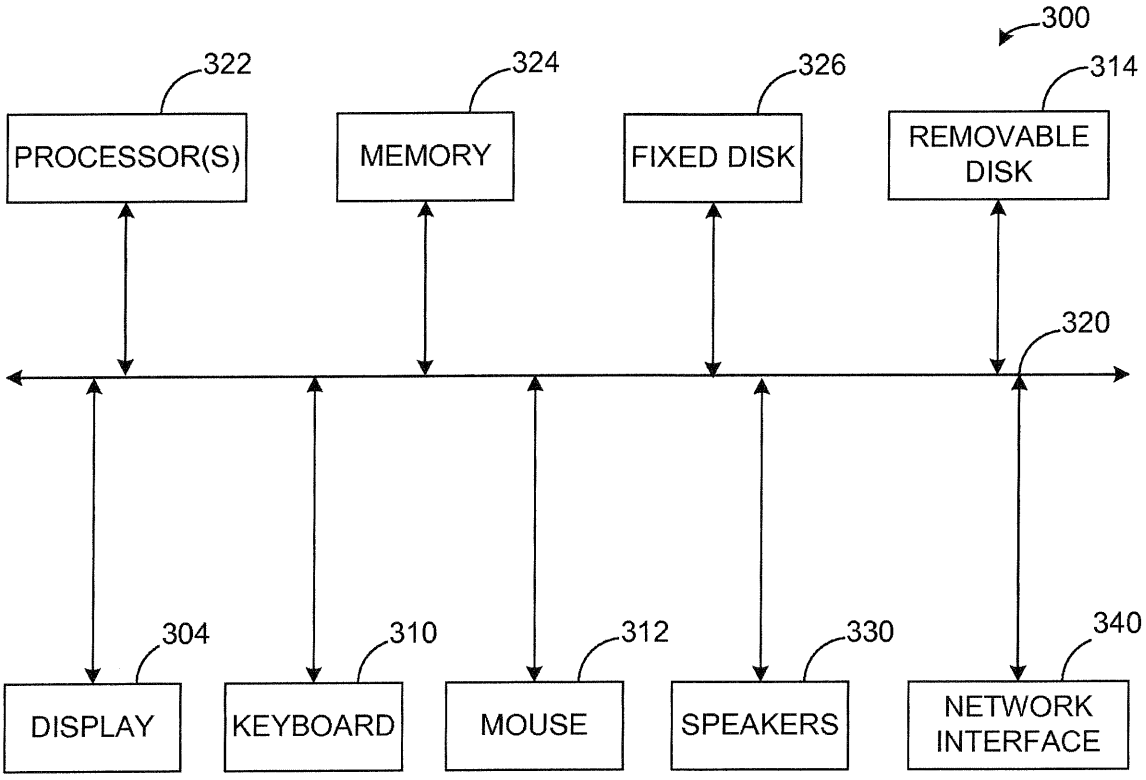

300
322
324
326
314
PROCESSOR(S)
MEMORY
FIXED DISK
REMOVABLE DISK
320
304
310
312
330
340
DISPLAY
KEYBOARD
MOUSE
SPEAKERS
NETWORK INTERFACE

FIG. 3B

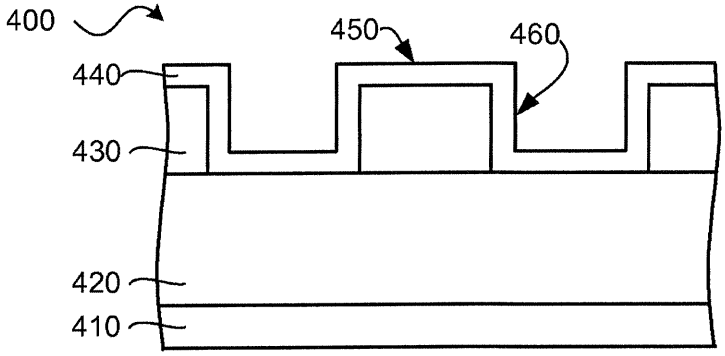


FIG. 4A

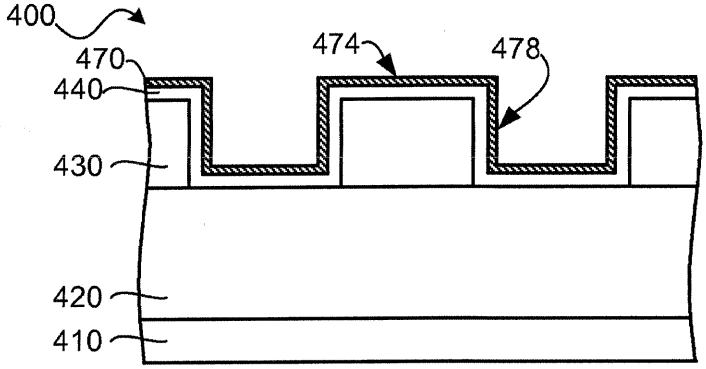


FIG. 4B

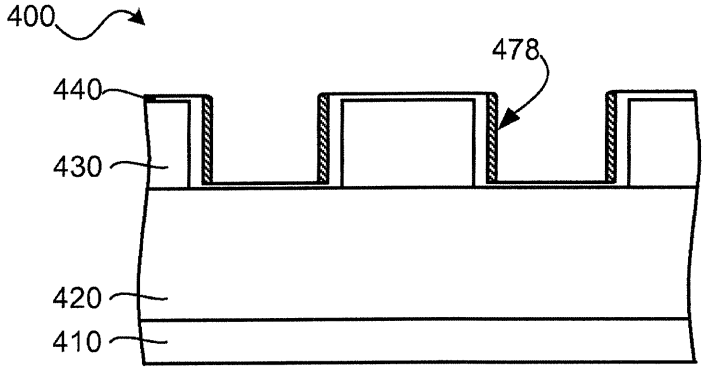


FIG. 4C

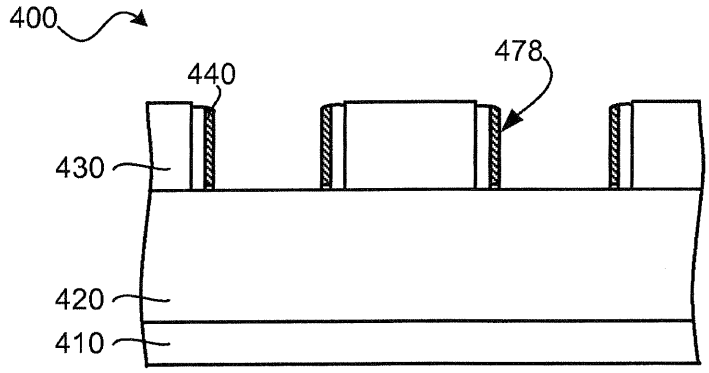


FIG. 4D

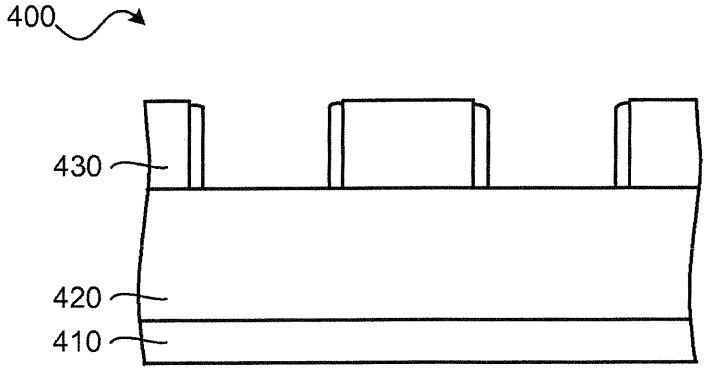


FIG. 4E